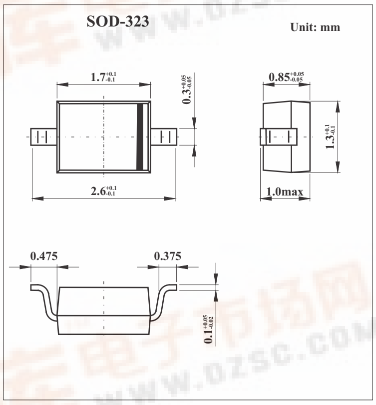
Silicon Epitaxial Planar Diode

1SV288



■ Features

- ● High Capacitance Ratio:C2V/C25V = 16(Typ.)
- ● Low Series Resistance:rs = 0.92 Ω (Typ.)
- ● Excellent C-V Characteristics,and Small Tracking Error.
- ● Useful for small size Tuner.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35(R_L = 10 K Ω)	V
Junction Temperature	T_j	125	℃
Storage Temperature Range	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R = 1 μ A	30			V
Reverse Current	I_R	V_R = 28 V			10	nA
Capacitance	C_{2V}	f = 1 MHz;V_R = 2 V	41		49.5	pF
	C_{25V}	f = 1 MHz;V_R = 25 V	2.5		3.2	
Capacitance Ratio	C_{2V}/C_{25V}		15	16		
Series Resistance	r_s	V_R = 5V, f = 470 MHz		0.92	1.05	Ω

Note :

Available in matched group for capacitance to 2.5%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leqslant 0.025$$

(V_R=2~25V)

■ Marking

Marking	TJ